Motivation: Integration of optical isolators with semiconductor devices
- Need complete crystallization for high optical quality
- Substrates require low thermal process

Results: Successful Integration with rapid thermal annealing (RTA)
- Furnace anneal requires 1000 °C for 0.5-3hrs.
- By RTA 800°C for less than 15-120 sec is sufficient.

Furnace anneal: 1000 °C, 3hr  
RTA: 800 °C, 120 sec